



TÉCNICO
LISBOA

Funcionalization of Si by ion- implantation:

Influence on the tribomechanical and wettability
properties at the micro and nano scales

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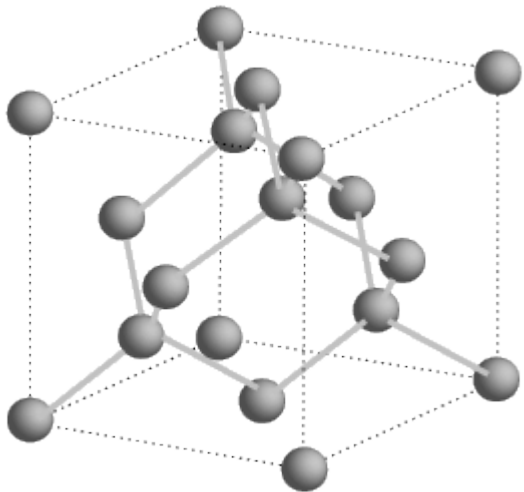
Encontro 2018 NanoLab/BioMat

Outline

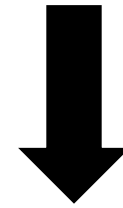
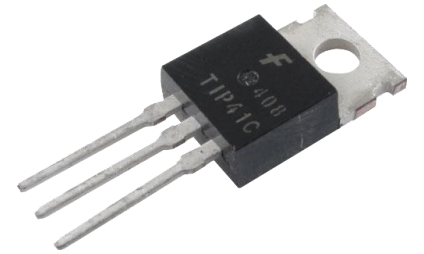
- Introduction
 - Motivation/objective
- Experimental Conditions
- Results & discussion
- Conclusions

Introduction

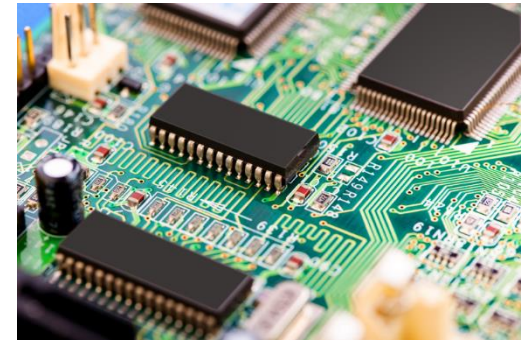
Why Silicon???



Transistor – electronic
revolution in th 60's



2D electronics – IC's

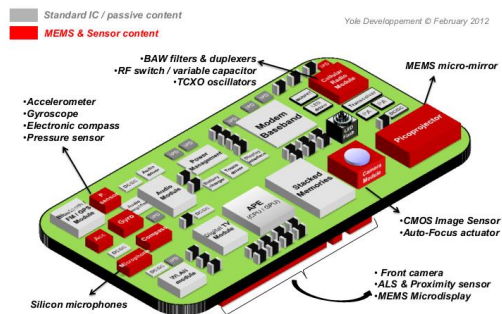
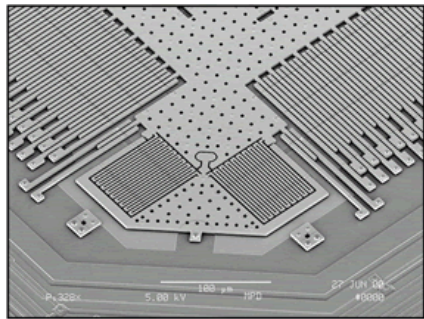


3D devices – MEMS

Introduction

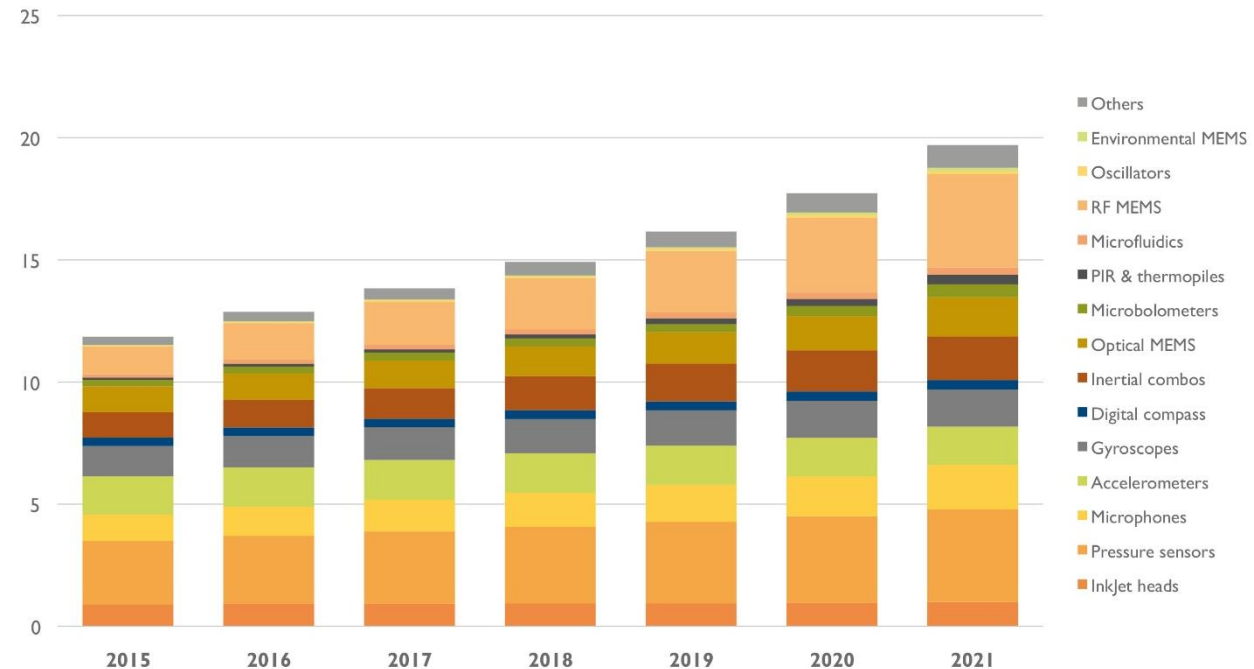
Microelectromechanical System (MEMS)

- Devices with a $100 \text{ nm} < L < 1 \text{ mm}$.
- Produced using IC's technologies.



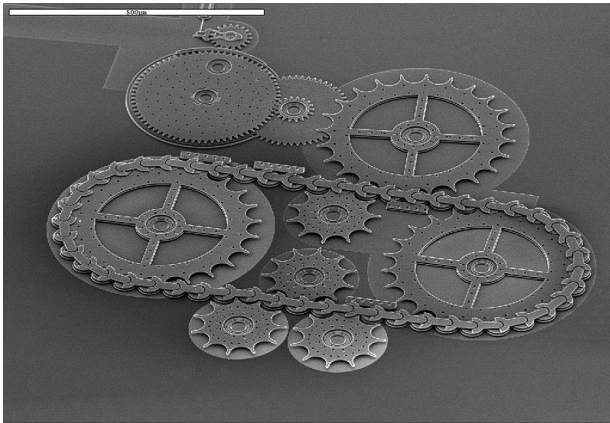
2015-2021 MEMS market forecast in US\$B

(Source: Status of the MEMS Industry report, Yole Développement, May 2016)

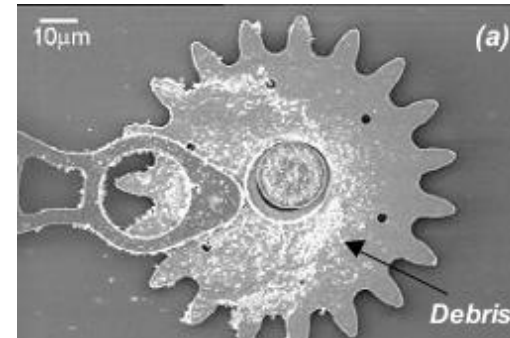
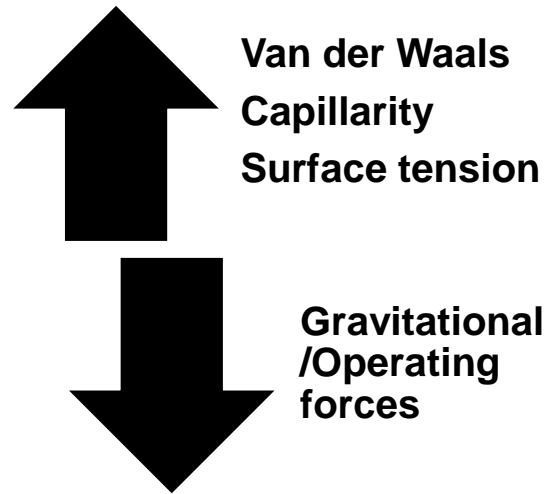


Objective

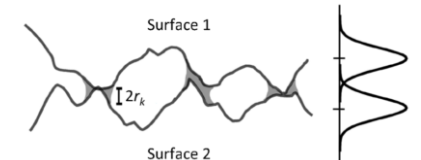
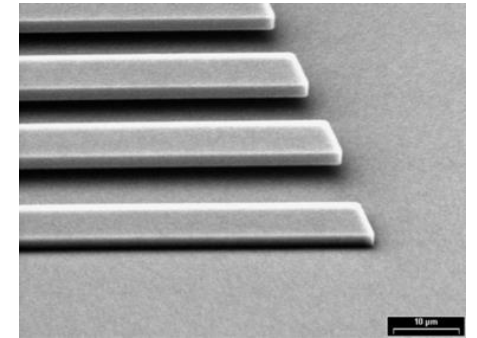
- Commercial MEMS do not have rubbing and impacting surfaces



Sandia Lab.



Tanner *et al.* 2002



Small dimensions
Scale effects $\frac{A}{V} \uparrow$

Failure mechanisms:
stiction and **high friction** resulting in
high wear

Si has **poor tribological /mechanical properties**

Enhance the tribomechanical and wettability properties of Si using Ion-implantation.

Experimental Conditions

Type	Element (Energy kev)	Fluence (cm ⁻²)	Conditions	Annealings (° C)
Single	Fe (150) C (25)	(low) 5×10^{15}	Room temperature & normal incidence	550
		(medium) 5×10^{16}		800
		(high) 2×10^{17}		1000
Dual	Fe (170) + C (50) Ti (160) + C (50)	(low) $5 \times 10^{16} + 5 \times 10^{16}$		800
		(high) $2 \times 10^{17} + 2 \times 10^{17}$		1000

Characterization Techniques

FEG-SEM/AFM

GIRXD ($\theta = 1.5^\circ$)

RBS/XPS

Wettability

Ultramicro hardness

AFM-based Nanowear

Results & Discussion – Fe⁺ Implantation

Medium Fluence $\Phi=5 \times 10^{16} \text{ cm}^{-2}$

High Fluence $\Phi=2 \times 10^{17} \text{ cm}^{-2}$

800 °C

1000 °C

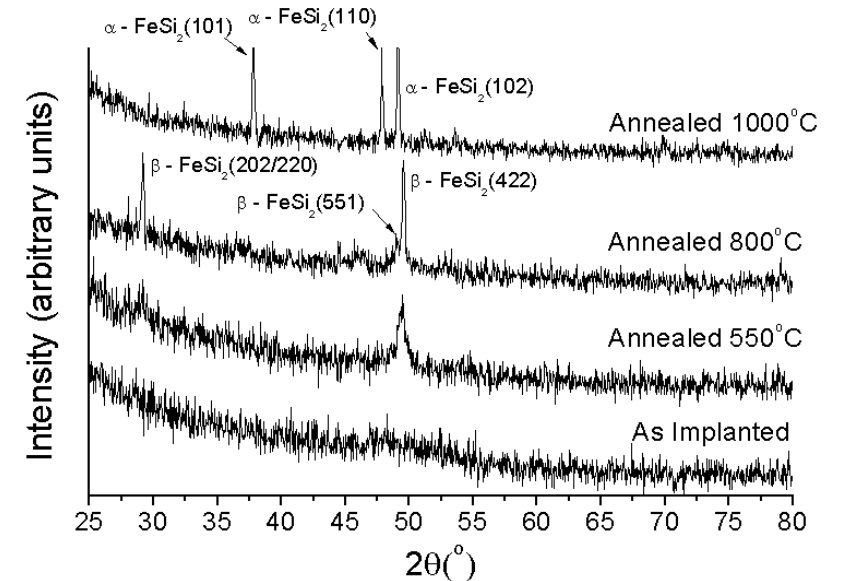
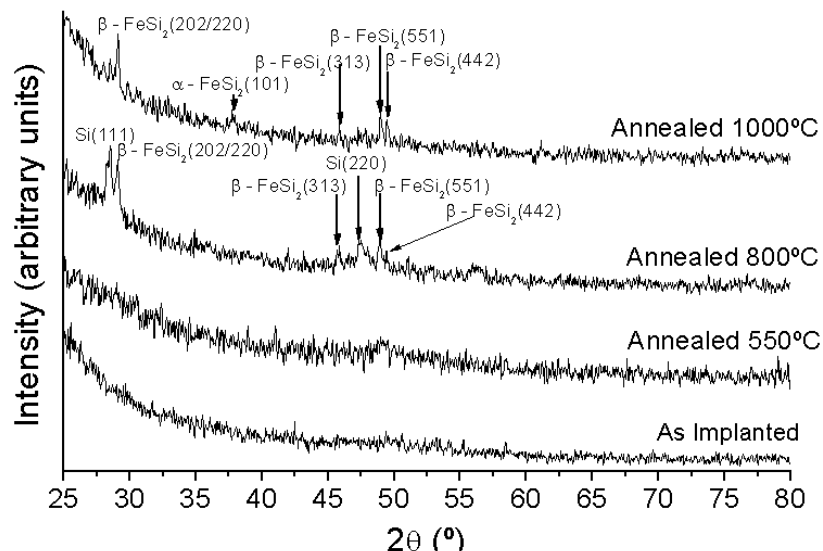
800 °C

1000 °C

Si

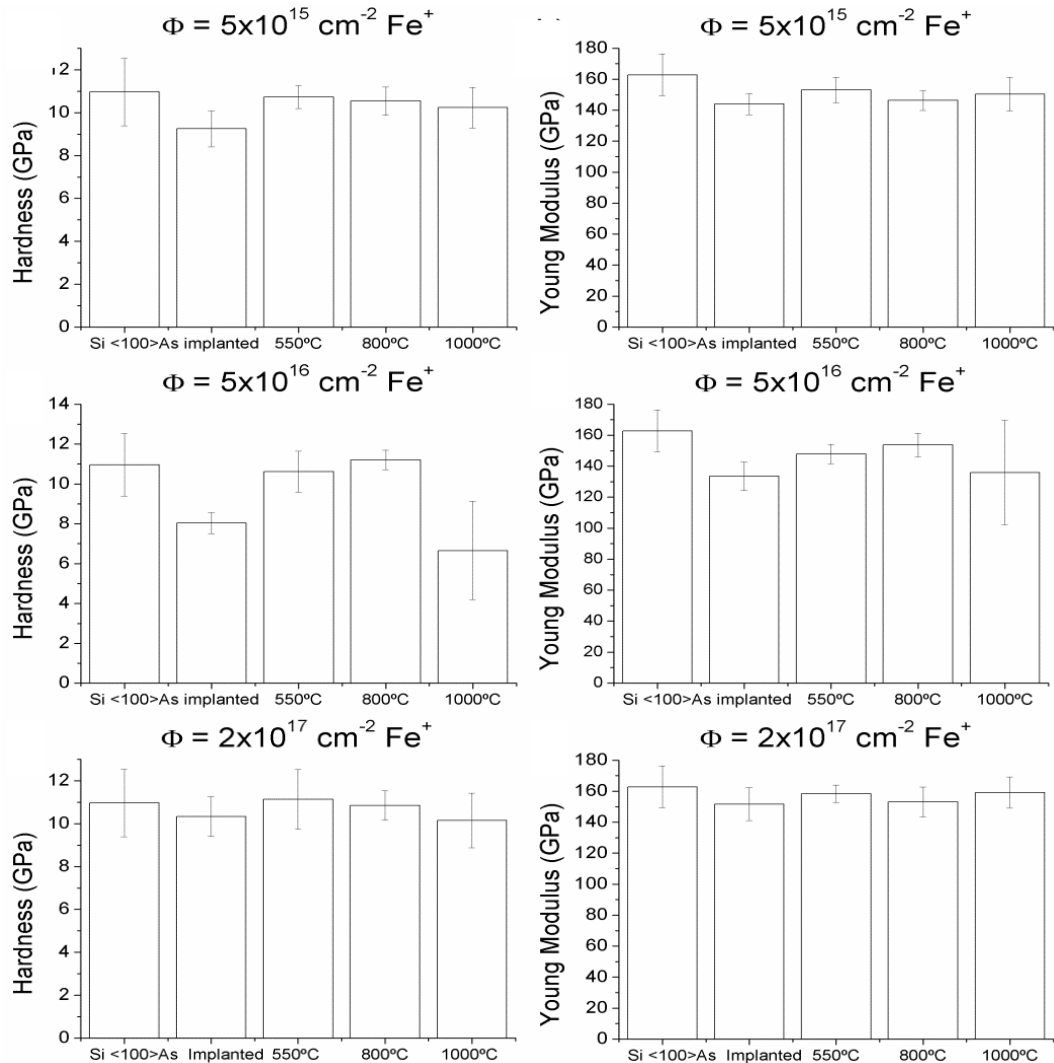
$\alpha - \text{FeSi}_2$

$\beta - \text{FeSi}_2$

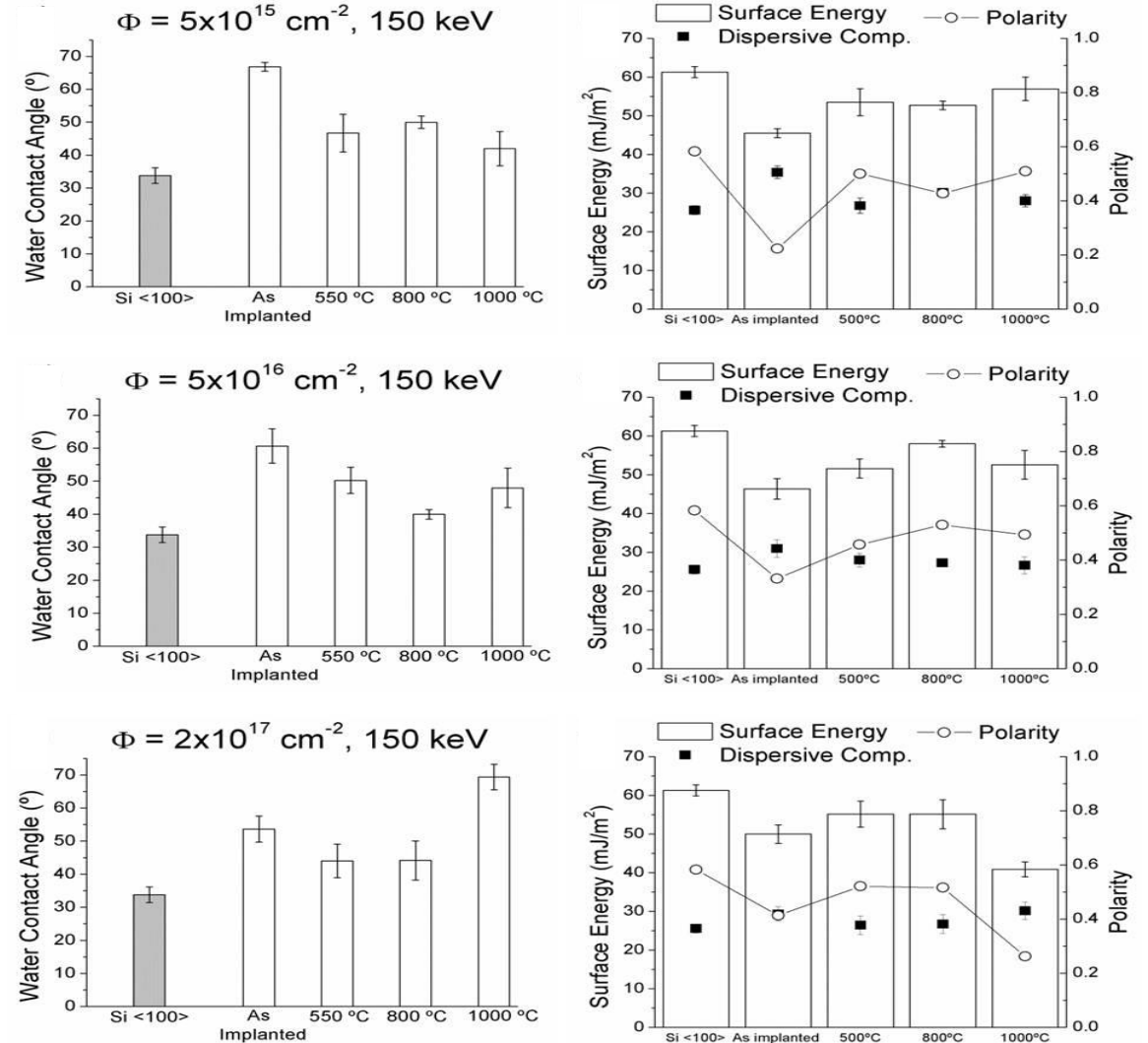


Results & Discussion – Fe⁺ Implantation

Ultramicrohardness (5 mN)

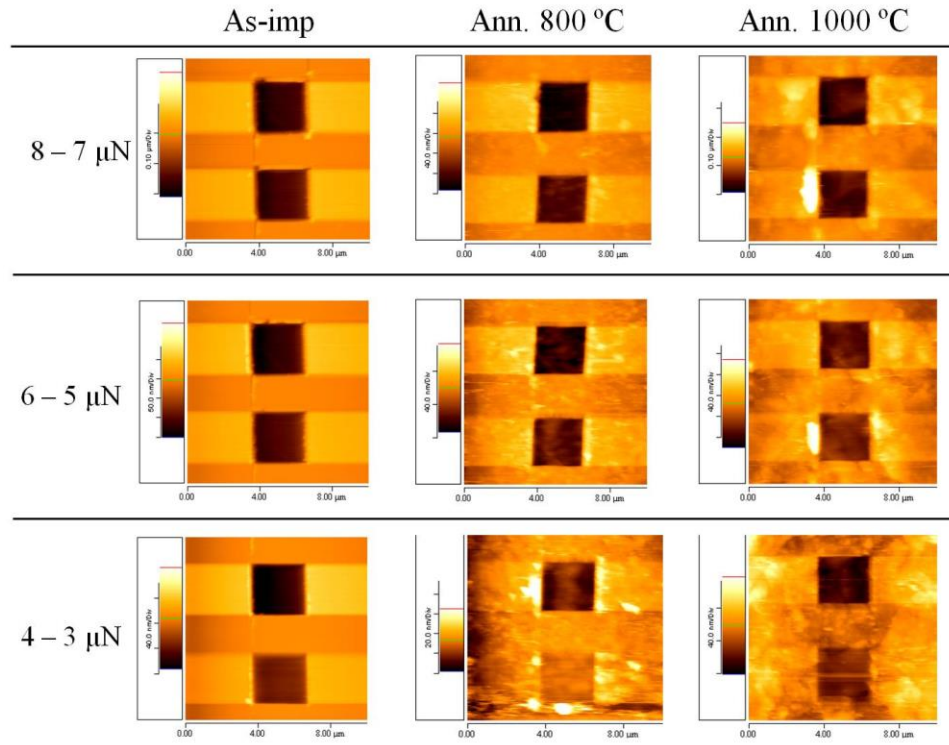
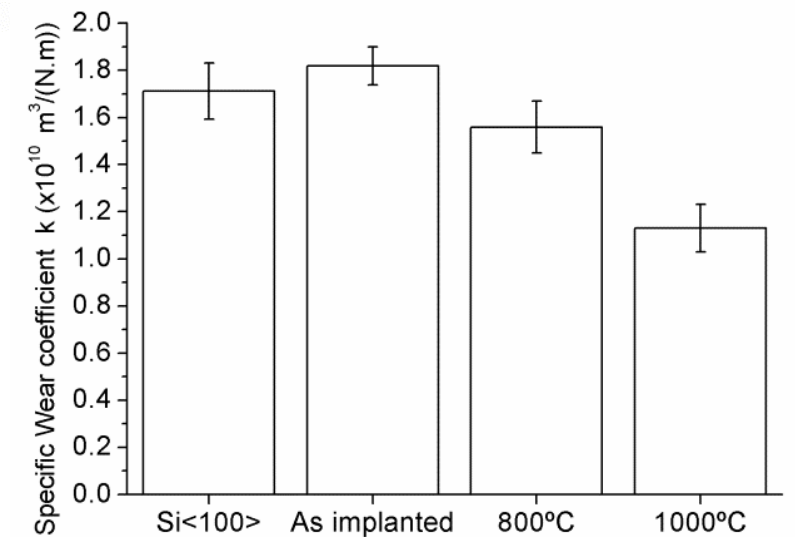
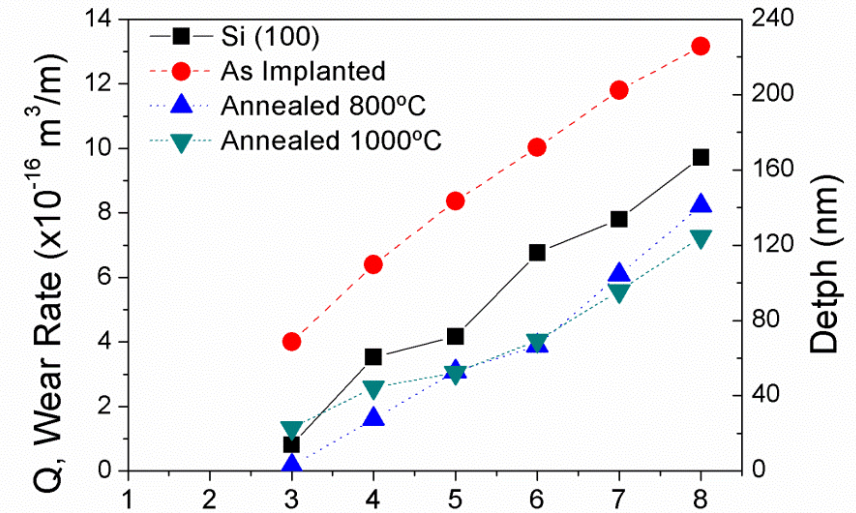
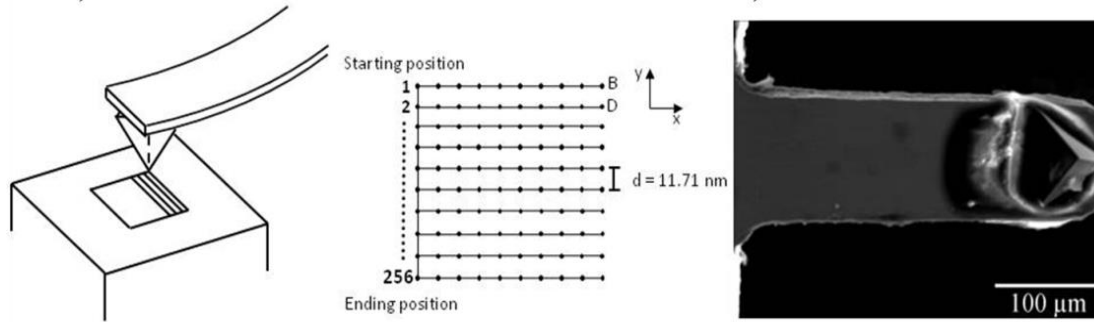


Contact angle and Surf. Energy



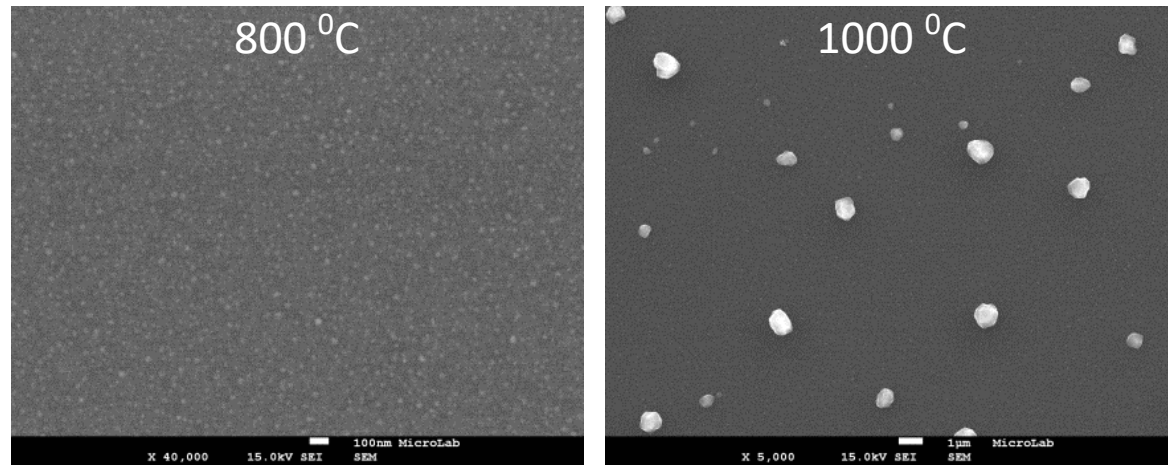
Results & Discussion – Fe⁺ Implantation

AFM-based Nanowear

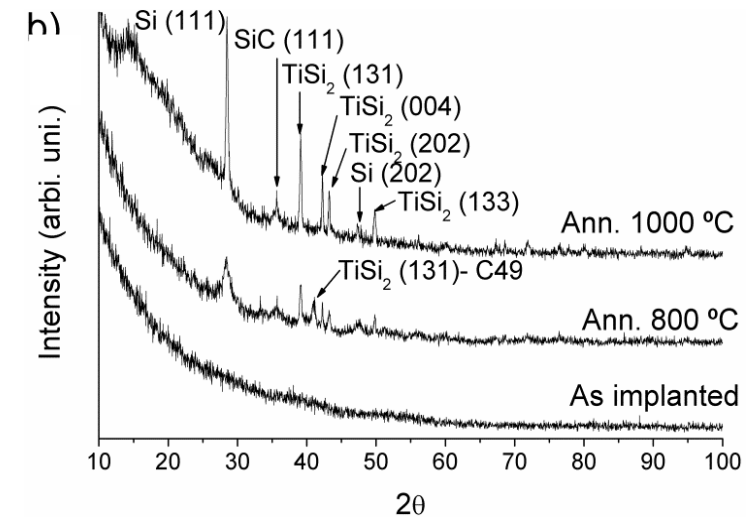
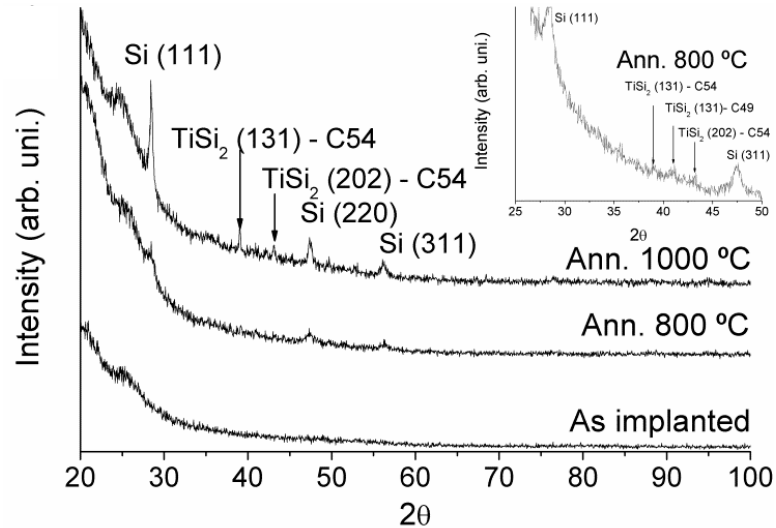
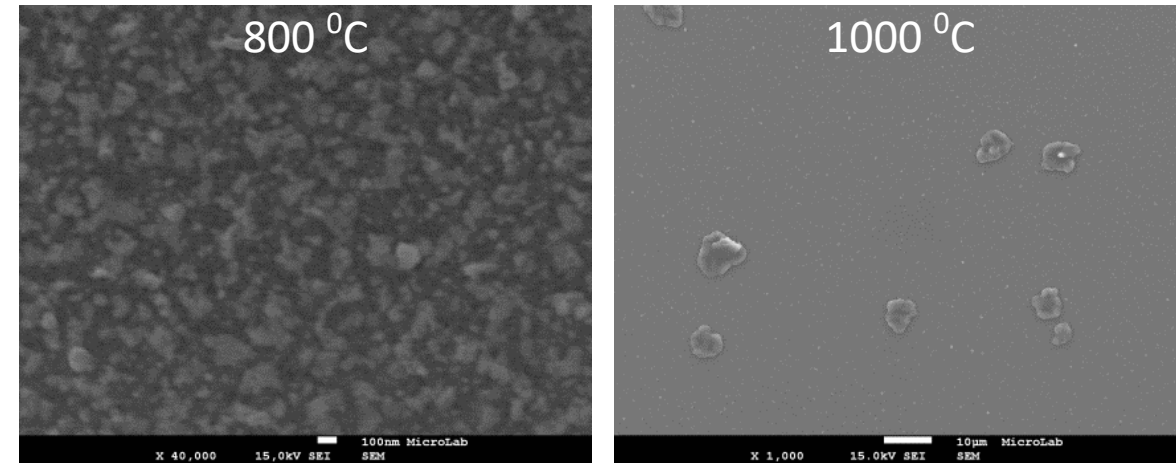


Results & Discussion – Ti⁺ + C⁺ Implantation

Medium Fluence $\Phi=5 \times 10^{16} \text{ cm}^{-2}$

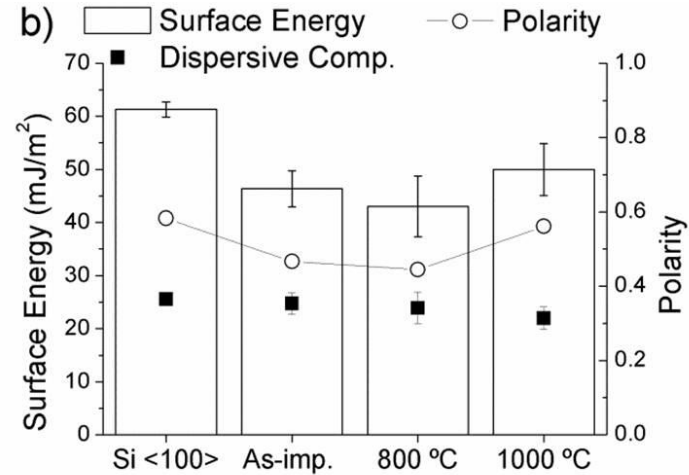
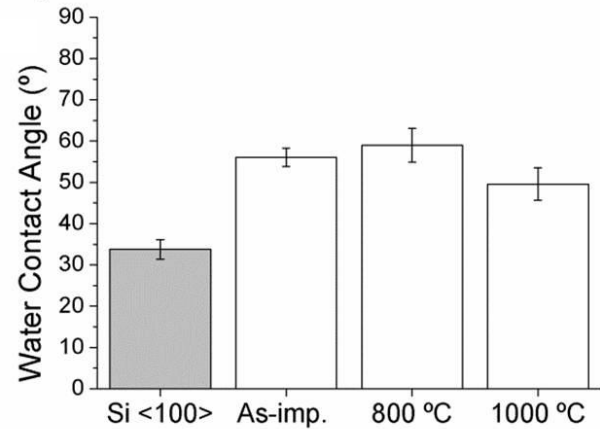


High Fluence $\Phi=2 \times 10^{17} \text{ cm}^{-2}$



Results & Discussion – Ti⁺ + C⁺ Implantation

a) $\Phi = 5 \times 10^{16} \text{ cm}^{-2}$ Ti⁺ 160 keV and C⁺ 50 keV



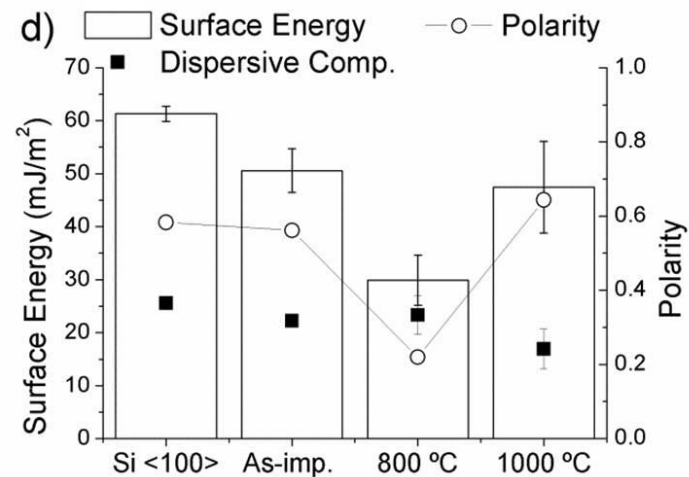
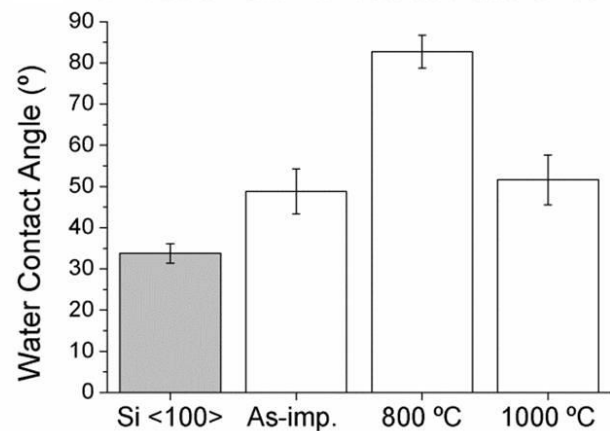
Low fluence

Identical values of θ even after the annealings

high fluence

The implanted and annealed samples present $> \theta$.

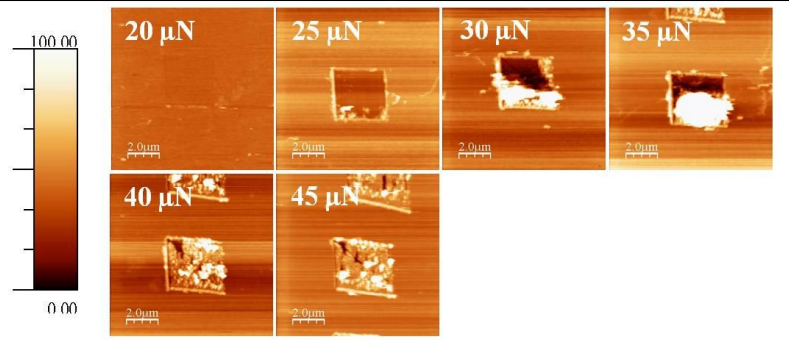
c) $\Phi = 2 \times 10^{17} \text{ cm}^{-2}$ Ti⁺ 160 keV and C⁺ 50 keV



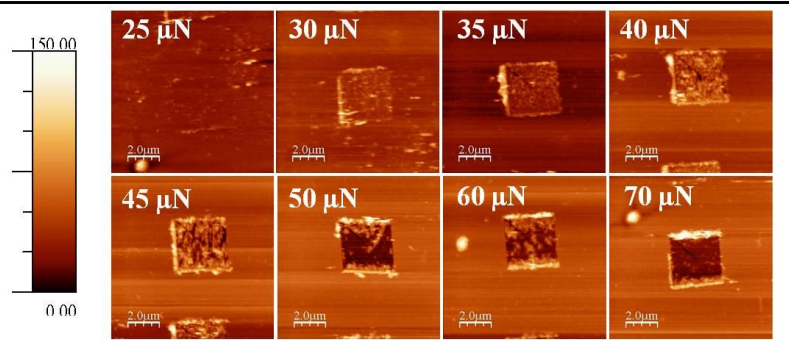
The 800 °C sample presented the higher contact angle.

Results & Discussion – Ti+ + C+ Implantation

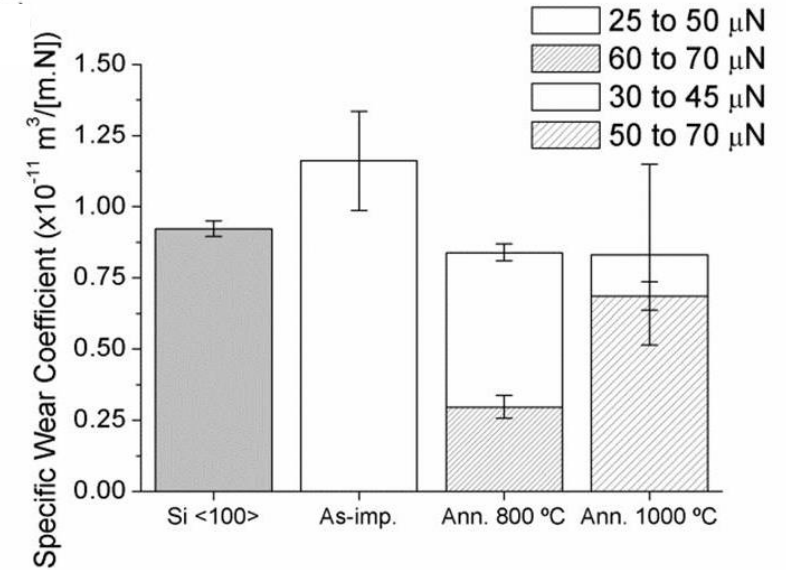
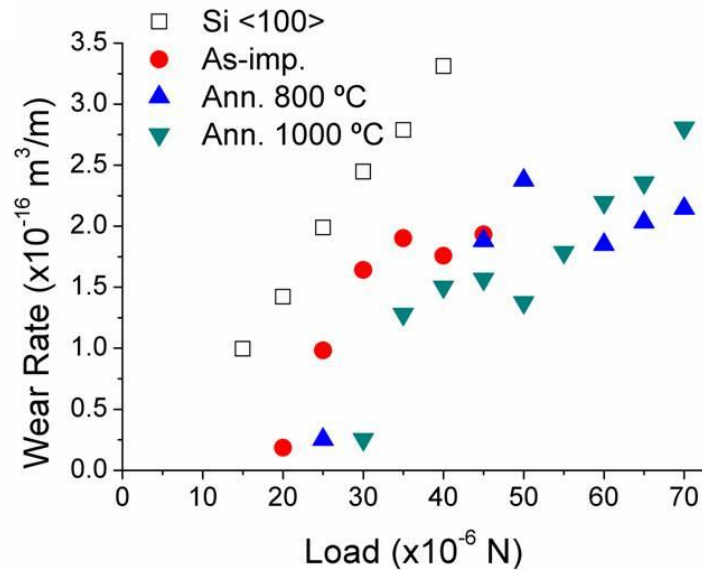
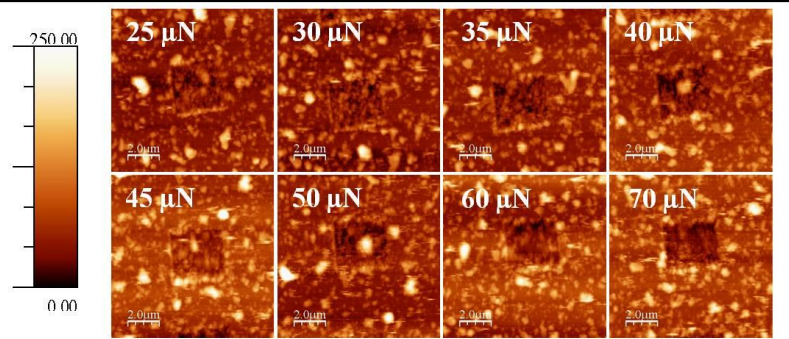
As-implanted



Ann. 800 °C



Ann. 1000 °C



Almost all the calculated Q's are below the Si

The combination of TiSi₂ and SiC greatly improve the nanowear resistance.

The lowest k was calculated for the 800 °C for the higher loads

Conclusions

- Wettability and Nanowear properties of Si can be upgraded using ion-implantation.
- From all the studied systems
 - The dual systems performed better than the single ones.
 - The single C+ revealed the poorest performance.
 - Low fluence Fe⁺⁺ C+ at 800 °C presented an almost hydrophobic behavior.
 - The Ti⁺⁺C+ system at 800 °C combine both high angle contact angle and low average specific wear coefficient.